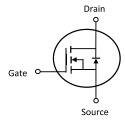
N Channel MOSFET





Device Schematic

RoHS Compliant



Applications

- · High Efficiency Switch Mode Power Supplies
- · Electronic Lamp Ballasts Based on Half Bridge
- · LED Power Supplies

Features

- RDS(ON) = 1.2Ω @ VGS = 10V
- Ultra Low Gate Charge
- · Low Reverse Transfer Capacitance
- Fast Switching Capability
- · Avalanche Energy Tested
- · Improved dv/dt Capability, High Ruggedness

Maximum Ratings @TA = +25°C

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	V _D s	650	V	
Gate-Source Voltage	Vgs	±30]	
Avalanche Current (Note 2.)	lar	7	7 7 A 29.6	
Continuous Drain Current	lo	7		
Pulsed Drain Current (Note 2.)	I _{DM}	29.6		
Single Pulsed Avalanche Energy (Note 3.)	Eas	530	mJ	
Repetitive Avalanche Energy (Note 2.)	Ear	14.2		
Peak Diode Recovery dv/dt (Note 4.)	dv/dt	4.5	V/ns	
Power Dissipation	PD	48	W	
Junction Temperature	Tj	150	°C	
Storage Temperature Range	Тѕтс	-55 to +150		

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

- 2. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
- 3. L = 19.5mH, Ias = 4A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 $^{\circ}$ C
- 4. IsD ≤ 7A, di/dt ≤ 200A/µs, VDD ≤ BVDSS, Starting TJ = 25°C

Newark.com/multicomp-pro Farnell.com/multicomp-pro sg.element14.com/b/multicomp-pro



N Channel MOSFET



Electrical Characteristics @TA = +25°C

Parameter	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
OFF Characteristics		•				•
Drain-Source Breakdown Voltage	Vgs=0V, Ip=250µA	Voss	650			V
Forward Gate-Source Leakage Current	V _{DS} =0V, V _{GS} =30V	lgss		1	100	nA
Reverse Gate-Source Leakage Current	V _{DS} =0V, V _{GS} =-30V			j	-100	
Drain-Source Leakage Current	Vps=650V, Vgs=0V	Inss			1	μΑ
Breakdown Voltage Temperature Coefficient	ID=250 μA,Referenced to 25μ	ΔBVpss/ΔTJ		0.67		
ON Characteristics	•	•				
Gate-Threshold Voltage	Vps=Vgs, lp=250µA	V _{th(GS)}	2		4	V
Static Drain-Source On-State Resistance	Vgs=10V, Ip= 3.5A	Rds(on)		0.94	1.2	Ω
Dynamic Characteristics	•	•				
Input Capacitance		Ciss	-		1400	
Output Capacitance	V _{DS} =25V, V _{GS} =0V, F=1MHz	Coss	-		018	pF
Reverse Transfer Capacitance	_	Crss	-	16	21	
Switching Characteristics	•	•				
Turn-On Delay Time		t _{D(ON)}	_		70	
Turn-On Rise Time	V _{DD} =325V, V _{GS} =7.4A, R _G =25Ω, (Note 1,2)	tr			170	ns
Turn-Off Delay Time		t _{D(OFF)}			140	
Turn-Off Fall Time	1	t⊧			130	1
Switching Characteristics		•				•
Total Gate Charge		QG		29	38	nC
Gate-Source Charge	Vps=520V, lp=7A, Vgs=10V (Note 1,2)	Qgs		7		
Gate-Drain Charge		QgD		14.5		
Drain-Source Diode Characteristics And N	laximum Ratings	•				
Drain-Source Diode Forward Volta	Is=7A, Vgs=0V	VsD			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	V _{GS} =0V, I _S =7A, dI _F /dt=-100A/µs (Note 1)	Is	-		7	A
Maximum Pulsed Drain-Source Diode Forward Current		Іѕм			29.6	
Reverse Recovery Time		trr		320		ns
Reverse Recovery Charge		Qrr		2.4		μC
Notes:1. Pulse Test:Pulse Width ≤300us,Duty 2. Essentially independent of operating	,					

Dimensions : Millimetres

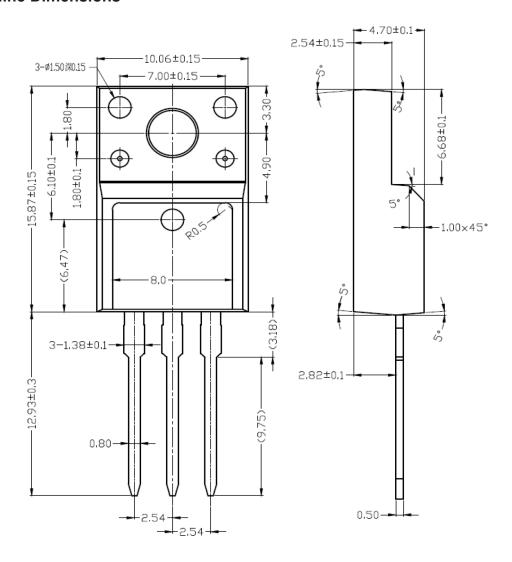




N Channel MOSFET



Outline Dimensions



Part Number Table

Description	Part Number		
N Channel MOSFET, 650V, 7A, TO-220F	HMF07N65S		

Important Notice: This data sheet and its contents (the "Information") belong to the members of the AVNET group of companies (the "Group") or are licensed to it. No licence is granted for the use of it other than for information purposes in connection with the products to which it relates. No licence of any intellectual property rights is granted. The Information is subject to change without notice and replaces all data sheets previously supplied. The Information supplied is believed to be accurate but the Group assumes no responsibility for its accuracy or completeness, any error in or omission from it or for any use made of it. Users of this data sheet should check for themselves the Information and the suitability of the products for their purpose and not make any assumptions based on information included or omitted. Liability for loss or damage resulting from any reliance on the Information or use of it (including liability resulting from negligence or where the Group was aware of the possibility of such loss or damage arising) is excluded. This will not operate to limit or restrict the Group's liability for death or personal injury resulting from its negligence. Multicomp Pro is the registered trademark of Premier Farnell Limited 2019.

Newark.com/multicomp-pro Farnell.com/multicomp-pro sg.element14.com/b/multicomp-pro

